

**IN THE SPECIFICATION**

Please replace paragraph [0001] of page 1 with the following paragraph [0001]:

**Related Application**

[0001] This application is related to U.S. Application Serial No. ~~(Attorney Docket No. 400.264US01)~~ filed \_\_\_\_\_, 200\_, 10/785,310 filed February 24, 2004, entitled “4F<sup>2</sup> EEPROM NROM MEMORY ARRAYS WITH VERTICAL DEVICES,” which is commonly assigned.

Please replace paragraph [0023] of page 6 with the following paragraph [0023]:

[0023] Figures 5A-5D and ~~5B~~ detail vertical NAND floating gate memory array and cells in accordance with embodiments of the present invention.